

1740nm InGaAs 1000um PD Chip datasheet

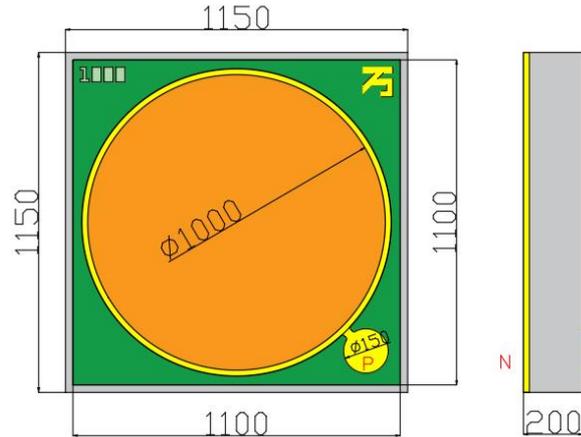
P/N : WIR3-1000

Feature

High responsivity
Low dark current
900-1740nm Spectral range

Structure

InGaAs / InP PIN Chip.
P Electrode (anode) : Gold.
N Electrode (cathode) : Gold.



DIMENSIONS

Conditions	Min.	Typ.	Max	Unit
Active	995	1000	1005	μm
Chip width	1130	1150	1170	μm
Chip length	1130	1150	1170	μm
Chip height	180	200	220	μm
Pad Area	140	150	160	μm

Electro-Optical Characteristics (@ Ta=25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Dark current	Id	Vr=-5V	-	0.5	2.5	nA
Capacitance	Cp	Vr=-5V	-	55	65	pF
Responsivity	R	@1654 nm	0.9	1	-	A/W
Wavelength range	λ		900	1650	1740	nm

PS. ESD (HBM) > 800V

ABSOLUTE MAXIMUM RATING

Parameter	Rating
Operating Temperature	-40°C to 85°C
Storage Temperature	-55°C to 125°C
Forward Current	10mA